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2SC2590

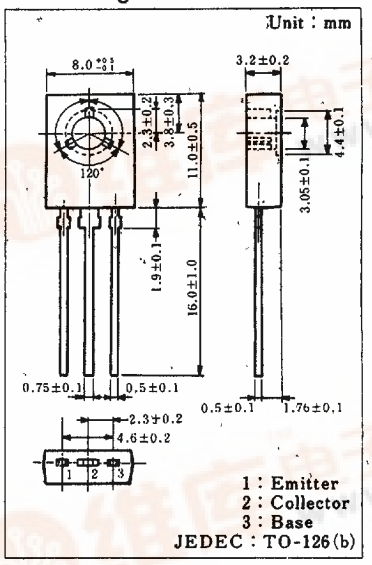
Silicon NPN Epitaxial Planar Type

AF Power Amplifier
Complementary Pair with 2SA1110

■ Features

- Very good linearity of DC current gain (h_{FE})
- High transition frequency (f_T)
- Optimum for the driver of 40~100W in complementary pair with 2SA1110

■ Package Dimensions



■ Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	1	A
Collector current	I_C	0.5	A
Collector power dissipation	P_C	1.2 *	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	−55~+150	℃

* Without heat sink

■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector-emitter voltage	V_{CEO}	I_C=100 μA, I_B=0	120			V
Emitter-base voltage	V_{EBO}	I_E=10 μA, I_C=0	5			V
DC current gain	h_{FE1} *1	V_{CE}=10 V, I_C=150 mA*2	65		330	
	h_{FE2}	V_{CE}=5 V, I_C=500 mA*2	65	100		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=300 mA, I_B=30 mA			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=300 mA, I_B=30 mA			1.2	V
Transition frequency	f_T	V_{CB}=10V, I_E=−50mA, f=200MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=10 V, I_E=0, f=1 MHz		11	20	pF

*2 Pulse measurement

*1 h_{FE1} Classifications

Class	P	Q	R	S
h_{FE1}	65~110	90~155	130~220	185~330

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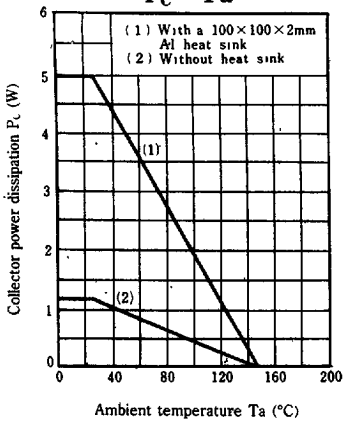
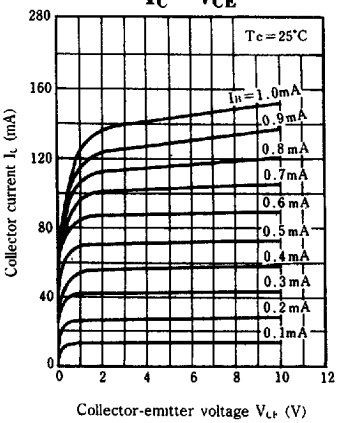
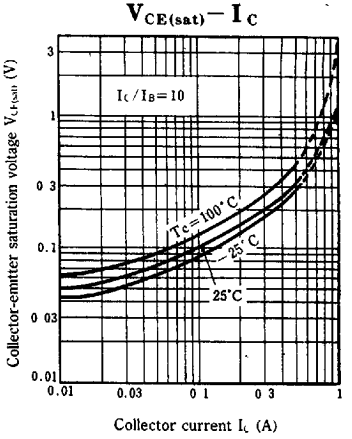
$P_C - Ta$



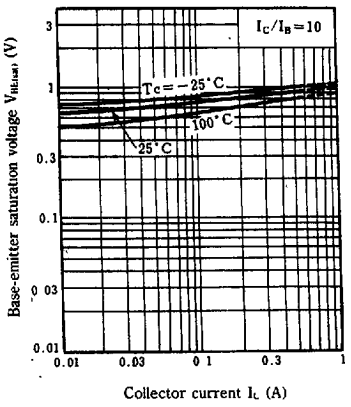
$I_C - V_{CE}$



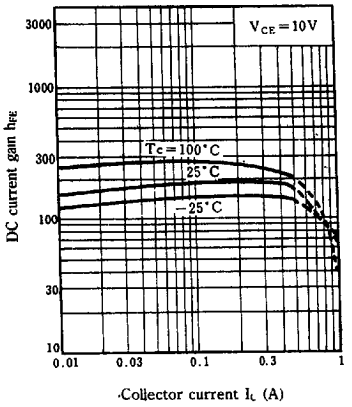
$V_{CE(sat)} - I_C$



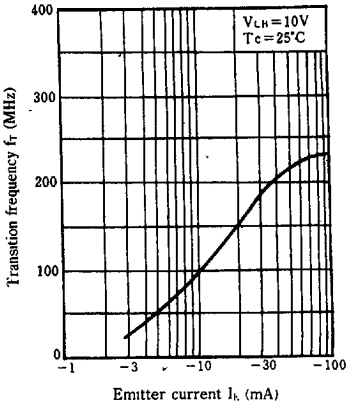
$V_{BE(sat)} - I_C$



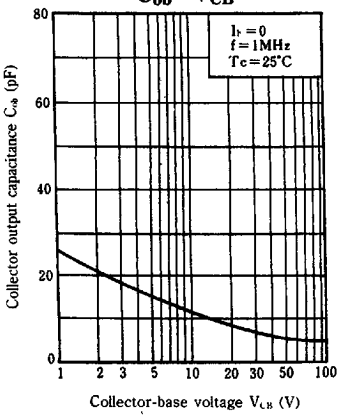
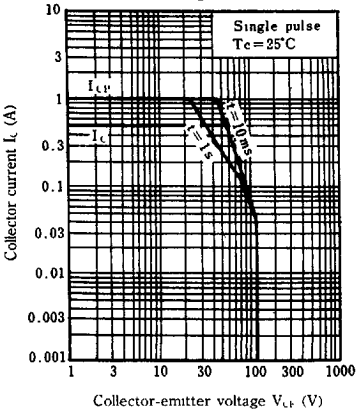
$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$



Area of safe operation (ASO)